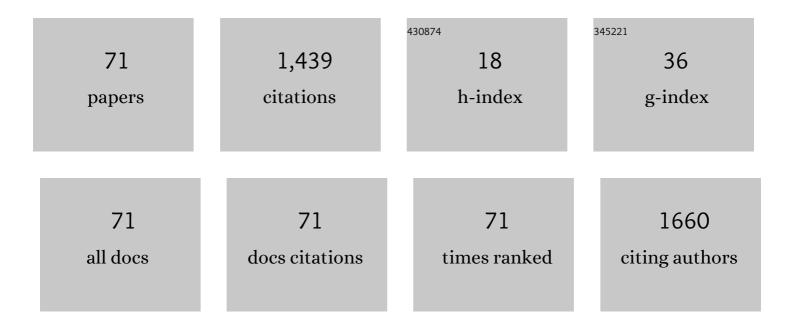
List of Publications by Year in descending order

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Υπκιμαρίι Πραφάλ

#	Article	IF	CITATIONS
1	Photographic surveying of minority carrier diffusion length in polycrystalline silicon solar cells by electroluminescence. Applied Physics Letters, 2005, 86, 262108.	3.3	436
2	Floating Nanodot Gate Memory Devices Based on Biomineralized Inorganic Nanodot Array as a Storage Node. Japanese Journal of Applied Physics, 2006, 45, L1-L3.	1.5	100
3	Floating nanodot gate memory fabrication with biomineralized nanodot as charge storage node. Journal of Applied Physics, 2008, 103, .	2.5	61
4	Novel Method for Making Nanodot Arrays Using a Cage-like Protein. Japanese Journal of Applied Physics, 2003, 42, L398-L399.	1.5	54
5	Electron confinement in a metal nanodot monolayer embedded in silicon dioxide produced using ferritin protein. Applied Physics Letters, 2006, 88, 023108.	3.3	54
6	Anomalously anisotropic channel mobility on trench sidewalls in 4H-SiC trench-gate metal-oxide-semiconductor field-effect transistors fabricated on 8° off substrates. Applied Physics Letters, 2007, 90, 042102.	3.3	50
7	Analysis of thermoelectric properties of amorphous InGaZnO thin film by controlling carrier concentration. AIP Advances, 2015, 5, .	1.3	44
8	Characteristics of Perovskite Solar Cells under Low-Illuminance Conditions. Journal of Physical Chemistry C, 2016, 120, 18986-18990.	3.1	43
9	Electrical and Optical Properties of Nickelâ€Oxide Films for Efficient Perovskite Solar Cells. Small Methods, 2020, 4, 2000454.	8.6	37
10	Interface Optoelectronics Engineering for Mechanically Stacked Tandem Solar Cells Based on Perovskite and Silicon. ACS Applied Materials & Interfaces, 2016, 8, 33553-33561.	8.0	36
11	Analysis of Anomalous Charge-Pumping Characteristics on 4H-SiC MOSFETs. IEEE Transactions on Electron Devices, 2008, 55, 2013-2020.	3.0	34
12	Effect of Gold Nanoparticle Distribution in TiO2 on the Optical and Electrical Characteristics of Dye-Sensitized Solar Cells. Nanoscale Research Letters, 2017, 12, 513.	5.7	27
13	Comprehensive study of electroluminescence in multicrystalline silicon solar cells. Journal of Applied Physics, 2009, 106, .	2.5	26
14	High-density carrier-accumulated and electrically stable oxide thin-film transistors from ion-gel gate dielectric. Scientific Reports, 2016, 5, 18168.	3.3	24
15	Low-temperature fabrication of solution-processed InZnO thin-film transistors with Si impurities by UV/O3-assisted annealing. AIP Advances, 2012, 2, .	1.3	20
16	Significant mobility improvement of amorphous In-Ga-Zn-O thin-film transistors annealed in a low temperature wet ambient environment. Applied Physics Letters, 2018, 112, 193501.	3.3	20
17	Charging and Coulomb staircase effects in silicon nanodisk structures fabricated by defect-free Cl neutral beam etching process. Applied Physics Letters, 2006, 89, 233127.	3.3	19
18	Characterizations of Al <sub>2</sub> O <sub>3</sub> gate dielectric deposited on nâ€GaN by plasmaâ€assisted atomic layer deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1426-1429.	0.8	19

#	Article	IF	CITATIONS
19	Thermoelectric Si1â^' <i>x</i> Ge <i>x</i> and Ge epitaxial films on Si(001) with controlled composition and strain for group IV element-based thermoelectric generators. Applied Physics Letters, 2020, 117, .	3.3	19
20	Experimental investigation of tunnel oxide thickness on charge transport through Si nanocrystal dot floating gate memories. Journal of Vacuum Science & Technology B, 2006, 24, 1271.	1.3	18
21	Low temperature cured poly-siloxane passivation for highly reliable <i>a</i> -InGaZnO thin-film transistors. Applied Physics Letters, 2018, 112, .	3.3	18
22	High-Performance Fully Solution-Processed Oxide Thin-Film Transistors via Photo-Assisted Role Tuning of InZnO. ACS Applied Electronic Materials, 2020, 2, 2398-2407.	4.3	17
23	Fabrication of Nanoshell-Based 3D Periodic Structures by Templating Process using Solution-derived ZnO. Nanoscale Research Letters, 2017, 12, 419.	5.7	16
24	Enhanced Thermoelectric Transport and Stability in Atomic Layer Deposited-HfO <sub>2</sub> /ZnO and TiO <sub>2</sub> /ZnO-Sandwiched Multilayer Thin Films. ACS Applied Materials & Interfaces, 2020, 12, 49210-49218.	8.0	16
25	Comparison between ZnO films grown by plasma-assisted atomic layer deposition using H2O plasma and O2 plasma as oxidant. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, 01A142.	2.1	15
26	Thermal reversibility in electrical characteristics of ultraviolet/ozone-treated graphene. Applied Physics Letters, 2013, 103, 063107.	3.3	14
27	H and Au diffusion in high mobility <i>a</i> -InGaZnO thin-film transistors via low temperature KrF excimer laser annealing. Applied Physics Letters, 2017, 110, .	3.3	14
28	A 3D Vertical-Channel Ferroelectric/Anti-Ferroelectric FET With Indium Oxide. IEEE Electron Device Letters, 2022, 43, 1227-1230.	3.9	14
29	Segregation-free bromine-doped perovskite solar cells for IoT applications. RSC Advances, 2019, 9, 32833-32838.	3.6	13
30	Unique degradation under AC stress in high-mobility amorphous In–W–Zn–O thin-film transistors. Applied Physics Express, 2020, 13, 054003.	2.4	13
31	Creating Reversible p–n Junction on Graphene through Ferritin Adsorption. ACS Applied Materials & Interfaces, 2016, 8, 8192-8200.	8.0	12
32	Instantaneous Semiconductor-to-Conductor Transformation of a Transparent Oxide Semiconductor a-InGaZnO at 45 °C. ACS Applied Materials & Interfaces, 2018, 10, 24590-24597.	8.0	12
33	Improvement in Bias Stress Stability of Solution-Processed Amorphous InZnO Thin-Film Transistors via Low-Temperature Photosensitive Passivation. IEEE Electron Device Letters, 2020, 41, 1372-1375.	3.9	12
34	Recover possibilities of potential induced degradation caused by the microâ€cracked locations in pâ€type crystalline silicon solar cells. Progress in Photovoltaics: Research and Applications, 2021, 29, 423-432.	8.1	10
35	Thermal distribution in amorphous InSnZnO thinâ€film transistor. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1561-1564.	0.8	9
36	Self-Heating Suppressed Structure of a-IGZO Thin-Film Transistor. IEEE Electron Device Letters, 2018, 39, 1322-1325.	3.9	9

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37	Evaluate Fixed Charge and Oxideâ€Trapped Charge on SiO <sub>2</sub> /GaN Metalâ€Oxideâ€Semiconductor Structure Before and After Postannealing. Physica Status Solidi (B): Basic Research, 2020, 257, 1900444.	1.5	8
38	Development of High-Reliability and -Stability Chemical Sensors Based on an Extended-Gate Type Amorphous Oxide Semiconductor Thin-Film Transistor. ACS Applied Electronic Materials, 2020, 2, 405-408.	4.3	8
39	Controlled charged amino acids of Ti-binding peptide for surfactant-free selective adsorption. Colloids and Surfaces B: Biointerfaces, 2014, 118, 25-30.	5.0	7
40	The Influence of Ga–OH Bond at Initial GaN Surface on the Electrical Characteristics of SiO 2 /GaN Interface. Physica Status Solidi (B): Basic Research, 2020, 257, 1900368.	1.5	7
41	Unseeded Crystal Growth of (100)-Oriented Grain-Boundary-Free Si Thin-Film by a Single Scan of the CW-Laser Lateral Crystallization of a-Si on Insulator. Crystals, 2020, 10, 405.	2.2	7
42	Improved Thermoelectric Power Factor of InGaZnO/SiOâ,, Thin Film Transistor via Gate-Tunable Energy Filtering. IEEE Electron Device Letters, 2021, 42, 1236-1239.	3.9	7
43	Characterization of local electrical properties of polycrystalline silicon thin films and hydrogen termination effect by conductive atomic force microscopy. Applied Physics Letters, 2009, 94, 182104.	3.3	6
44	Highly reliable passivation layer for a-InGaZnO thin-film transistors fabricated using polysilsesquioxane. Materials Research Society Symposia Proceedings, 2014, 1633, 139-144.	0.1	6
45	Biotemplated Synthesis of TiO <sub>2</sub> -Coated Gold Nanowire for Perovskite Solar Cells. ACS Omega, 2017, 2, 5478-5485.	3.5	6
46	Selection of a novel peptide aptamer with high affinity for TiO2-nanoparticle through a direct electroporation with TiO2-binding phage complexes. Journal of Bioscience and Bioengineering, 2016, 122, 528-532.	2.2	5
47	Hot Carrier Effect in UltraThin Gate Oxide Metal Oxide Semiconductor Field Effect Transistor. Japanese Journal of Applied Physics, 2005, 44, 5889-5892.	1.5	3
48	Effects of Si and Ti impurities on electrical properties of sol–gel-derived amorphous SrTa2O6 thin films by UV/O3 treatment. Applied Physics A: Materials Science and Processing, 2013, 112, 425-430.	2.3	3
49	Feasible control of laser doping profiles in silicon solar cell processing using multiple excitation wavelengths. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	2
50	ZnO Thin Film Transistors Fabricated by Atomic Layer Deposition Method. Materials Research Society Symposia Proceedings, 2009, 1201, 237.	0.1	2
51	Floating Gate Memory With Biomineralized Nanodots Embedded in \$hbox{HfO}_{2}\$. IEEE Nanotechnology Magazine, 2011, 10, 576-581.	2.0	2
52	Voltage Linearity and Leakage Currents of Crystalline and Amorphous SrTa2O6Thin Films Fabricated by Sol-Gel Method. Ferroelectrics, 2011, 421, 82-87.	0.6	2
53	Charge effects of ultrafine FET with nanodot type floating gate. , 2016, , .		1
54	Photo-assisted Processing of Amorphous Gallium Oxide (a-GaOx) Thin Film for Flexible and Transparent Device Application. , 2020, , .		1

#	Article	IF	CITATIONS
55	Orientation dependent etching of polycrystalline diamond by hydrogen plasma. Applied Physics Letters, 2022, 121, 021903.	3.3	1
56	Low Temperature Synthesis of Nanocrystalline Silicon and Silicon Oxide Films by Plasma Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 2008, 1066, 1.	0.1	0
57	Fabrication of PbTiO <inf>3</inf> and Pt self-organized nanocrystal array structure on atomically flat sapphire. , 2011, , .		0
58	Effect of high-pressure deuterium oxide annealing on Al <inf>2</inf> 0 <inf>3</inf> deposited by plasma-assisted atomic layer deposition at low temperature. , 2012, , .		0
59	Characterization of graphene based field effect transistors using nano probing microscopy. , 2012, , .		0
60	Hydrogen behavior from ALD Al <inf>2</inf> 0 <inf>3</inf> passivation layer for amorphous InGaZnO TFTs. , 2014, , .		0
61	Oxidation of graphene film by non-thermal treatment for new sensing devices. , 2014, , .		0
62	Unseeded growth of poly-crystalline Ge with (111) surface orientation on insulator by pulsed green laser annealing. , 2015, , .		0
63	Numerical modeling of device structure for FeS <inf>2</inf> thin film solar cells. , 2016, , .		0
64	Internal resistance of perovskite solar cells under low illuminance conditions. , 2016, , .		0
65	Thermoelectric Conversion Devise Using Ga-Sn-O Thin Film Prepared by Mist CVD Method. , 2018, , .		0
66	Reliability Enhancement of Solution Processed Amorphous In-Zn-O Thin-Film Transistors via a Low Temperature (180 °C) Solution Processed Passivation. , 2018, , .		0
67	Threshold Voltage Control of In-Ga-Zn-O TFT without Thermal Annealing Process by Inductively Coupled Plasma Sputtering System. , 2018, , .		0
68	High reliability InGaZnO TFT by inductively coupled plasma sputtering system. , 2019, , .		0
69	Performance Enhancement of Solution-Processed In-Zn-O Thin-film Transistors via Low-Temperature Wet Annealing Ambients. , 2021, , .		0
70	OS06-2-3 Carbon nanotubes-embedded MEMS resonator device for hydrogen gas sensing system. The Abstracts of ATEM International Conference on Advanced Technology in Experimental Mechanics Asian Conference on Experimental Mechanics, 2011, 2011.10, _OS06-2-3	0.0	0
71	Forming Fe nanocrystals by reduction of ferritin nanocores for metal nanocrystal memory. AIP Advances, 2022, 12, 055029.	1.3	0